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SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

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A semiconductor device suppressing the lateral diffusion of impurities doped in a PMOS and NMOS and shortening the distance between the PMOS and NMOS to reduce the size of the semiconductor device, including PMOS and NMOS formation regions isolated by an element isolation region; a p-type gate electrode arranged on the PMOS formation region; an n-type gate electrode arranged on the NMOS formation region; and first and second impurity storage regions arranged in a direction different from that of the arrangement of the p-type and n-type gate electrodes. An end of the first impurity storage region is connected to the p-type gate electrode, an end of the second impurity storage region is connected to the n-type gate electrode, and the other ends of the first and second impurity storage regions are electrically connected.